EE_735 Assignment 3: Additional material

Steps to solve poisson's equation using newton-raphson method:

1. Descretize the given device length in N nodes:



- 2. Define the dopant profile.
- 3. Assign initial potential profile V_{old} (it is Nx1 matrix) with boundary conditions applied at nodes 1 and N.
- 4. Write Poisson's equation for the ith node:

$$\frac{V_{i-1} - 2V_i + V_{i+1}}{h^2} = -\frac{\rho_i}{\varepsilon} \tag{1}$$

where, ρ_i is a function of V_i

a) Form the expression

$$F_i = F(V_i) = \frac{V_{i-1} - 2V_i + V_{i+1}}{h^2} + \frac{\rho_i}{\varepsilon}$$
 (2)

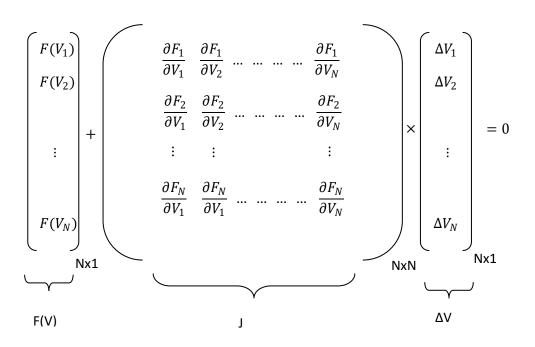
b) Assume $(V_i + \Delta V_i)$ to be the root of (2), then

$$F(V_i + \Delta V_i) = 0$$

c) Using Taylor's series expansion and neglecting second and higher order terms in ΔV_i

$$F(V_i + \Delta V_i) = F(V_i) + \sum_{j=1}^{N} \frac{\partial F(V_i)}{\partial V_j} \Delta V_j = 0$$
 (3)

5. Obtain equation (3) for all the nodes. Thus a set of 'N' non-linear equations is obtained which in the matrix representation can be shown as



where J is termed as the Jacobian matrix.

6. Obtain a solution for ΔV as

$$\Delta V = -J \backslash F(V) \tag{4}$$

7. Obtain new potential profile as

$$V_{new} = V_{old} + \Delta V \tag{5}$$

Make sure that the boundary conditions don't get changed while you update the potential profile.

- 8. Obtain F(V) and J for V_{new} .
- 9. Repeat steps 6 to 8 for sufficiently large number of iterations or till ΔV goes below some predefined tolerance value.